Cadence AWR Design Environment Empowers RF PA Design and Simulation RF Design Solutions for High-Power Amplifiers

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Agenda

GaN RF Design Trends and Challenges

Cadence Solution in RF Design

Design and Simulation

RF Packaging and Thermal Analysis

Rohde Schwarz – Cadence Collaboration

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Summary



GaN RF Design Trends and Challenges



Benefits of GaN for RF Applications



GaN for PA Design

	Property	Si	GaAs	SiC	GaN	
	Energy Gap (eV)	1.11	1.43	3.2	3.4	High Voltage
	Critical Electric Field (MV/cm)	0.6	0.5	3.0	3.5	Voltage
	Charge Density (# x 1x10 ¹³ /cm ²)	0.3	0.3	0.4	1	High High Current 🗭 Power
	Thermal Conductivity (W/cm/K)	1.5	0.5	4.9	1.5	Density Amp
N	Mobility (cm²/V/s)	1300	6000	600	1500	High
	Saturation Velocity (x 10 ⁷ cm/s)	1	1.3	2	2.7	Frequency

• GaN Is Natural Fit For High Power Applications

Simulation and Design Tools Needed for an Effective Design Process

- Load pull analysis built into the design framework
 - Graphing capabilities to display load pull-based behavior in a convenient manner
- Nonlinear stability analysis tools
- Matching circuit synthesis
 - Input and Out matching circuits need to be synthesized
- Electromagnetic (EM) and circuit co-simulation



Cadence Solution in RF Design



Cadence Silicon RFIC, MMIC, and SiP Solutions

Design, analyze, and implement

Platform	AWR Design Environment®	Cadence
Technologies	 GaN/GaAs and Si MMIC Chips, Acoustic modules Smaller mmW and uW Si RFIC Blocks 	 Si RFIC and Digital Chips SiP and Heterogeneous Integration
Design	 Microwave Office[®] w/ APLAC Visual System Simulator[™] 	Virtuoso w/ Spectre®
Analysis	 EMX[®], AXIEM[®] (planar EM) Clarity[™], Analyst (3D FEM) Celsius[™] (Thermal) 	 EMX, AXIEM (planar EM) Clarity, Analyst (3D FEM) Celsius (Thermal) Innovus[™]
Implementation	Front-to-back for MMICInteroperability to Virtuoso for backend	Front-to-back for RFIC, SoC, SiP

Complete System-Level RF-Aware Design Platform

Efficient, reliable, extensible RF design and analysis from transistors to antennas

High-Performance RF Design Solution



Wireless and Radar Design

- Optimized IC, package, and PCB workflows
- Integrated design data exchange
- Seamlessly embedded multiphysics analysis

Only with Cadence

- Up to 5X designer productivity
- Eliminate point tool interoperability friction
- Quick turnaround system analysis

Design, Analysis, and Implementation Solutions



GaN PDK Partnerships

Global support of GaN foundries and integrated device manufacturers

- PDKs available from leading GaN, GaAs, SiGe, and silicon foundries
- Co-developed with foundries serving both commercial and aerospace/defense markets
- Global reach across North America, EMEA, and AP regions
- Feature-rich PDKs include:
 - Symbols and schematics
 - Fully-scalable Pcells
 - Scalable models nonlinear GaN transistor (HEMT, pHEMT) models for amplification and switching
 - Monte Carlo statistical/mismatch simulation
 - Advanced layout utilities
 - Accurate EM simulation featuring:
 - EM-enabled parameterized on-chip passives
 - Predefined substrate definitions and stack-ups with geometry simplification

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Preconfigured simulation settings



Design and Simulation



RF Power Amplifier Design Flow



Simulation and Modeling Capabilities

Analysis for all phases of RF circuit design and verification

- DC IV
- Linear S-parameters
- Stability
- Harmonic balance
- Circuit envelope
- Load/source pull
- Yield
- Optimization
- EM analysis



Load-Pull Analysis for Power Amplifier Design

Determine load requirements for challenging specifications

- Simulate nonlinear performance as a function of source and/or load impedance.
- Plot performance contours such as P_{out}, PAE
 - Provides key design information for matching circuit development
 - Supports nested source/load harmonic load-pull
 - Supports low-frequency (F2-F1) load-pull for twotone excitations (new in v15)
- Can be performed over swept power, frequency, or other user-defined parameters



Load-Pull Analysis for PA



Network Synthesis Wizard

- <u>Synthesis Definition</u> defines the "direction" of the matching network and frequency band(s) of interest
- <u>Components</u> defines the available series and shunt components as well as first component and last component limitations
- <u>Parameter Limits</u> defines the parameter limits, parameter rounding, component series, etc. for each component
- <u>DC and Bias Feed</u> defines the matching network DC path constraints and the bias injection network that the wizard should consider
- <u>Goals</u> defines the measurements and goals for the synthesis. Double-click on a Measurement or Goal to see the setup.
- <u>Search Options</u> defines advanced search options
- <u>Results</u> Shows Synthesis run results and controls how many networks and what additional data is sent back to Microwave Office[®] software



Linear and Nonlinear Stability Analysis This wizard guides you through the steps that are needed in analyzing the stability of the selected circuit using the STAN stability analysis. The STAN approach enables nonlinear stability analysis so the circuit stability can be studied for example as a function of swept power. Each sweep point performs an HB analysis which is followed by a set of small signal analysis over the chosen frequency band. The data gathered from each stability probe will be sent to STAN which returns the identified poles and zeros shown in MWO graphs. IVCAD with STAN and Scripting plugins is needed to analyze the data. Linear Internal Stability Analysis Read more NLSTABILITY L1<<100 W1<<40 C<<5 ID=ST1 >VDS2 Stability Sweep Definitions Fstart=1000 MHz SUBCKT Circuit schemati Fend=10000 MHz STAB PROBE D=S6 D=SP1 NET="Output_Mat Select the circuit schematic for Stability Analysis Fsteps=10 L1=1:1 SwpType=LINEAR SUBCK *** NO VALID SCHEMATICS FOUND *** D=S4 ID=S5 NET="Input_Match NET#"LDMOS Mod This wizard requires at least one unlocked Circuit Schematic with - enabled port(s) and enabled named connector(s) or STAB_PROBE element(s). . MMIC Power Gain PORT in March NL Stability_STAN_RESULTS_NONLIN_S3_S1_STAB_PROBE_Drain_Probe P=2 Z=50 Ohm D=GP2 SUBCKT NL Stability_STAN_RESULTS_NONLIN_S3_S2_STAB_PROBE_Drain_Probe ID=S1 NET="LMDOS Packaged Model" ² **. . .** / . NL Stability_STAN_RESULTS_NONLIN_S3_S3_STAB_PROBE_Drain_Probe STAB PROBE GPROBE2 ID=SP1 TYPE=Current DIFFERENTIAL **Doherty Pair Stability Probe Results** market in the second sec PORT P=3 Z=50 Ohm 1.5 oles(STAB PROBE.Gate Probe,0)[*] (MHz) im NL Stability_STAN_RESULTS_NONLIN_S3_S8_STAB_PROBE_Drain_Probe bility STAN AP HB in ML Stability_STAN_RESULTS_NONLIN_STAB_PROBE_Gate_Probe STANZeros(STAB_PROBE.Gate_Probe,0)[*] (MHz) NL Stability STAN.AP HB 1 p2: Freq = 1.1e+004 Pwr = 10.5 dBm Freq = 1.1e+004 MHz Pwr = 10 dBm NL Stability STAN RESULTS NONLIN STAB PROBE Gate Probe 8: Freq = 1.1e+004 MHz p4: Freq = 1.1e+004 MHz Pwr = 11 dBm Pwr = 11.5 dBm 10000 5: Freq = 1.1e+004 MHz p8: Freq = 1.1e+004 MHz Pwr = 12 dBm Pwr = 12.5 dBm 0.5 5000 NL Stability_STAN_RESULTS_NONLIN_STAB_PROBE_Gate_Probe × ×xxxxxxxx 10000 0 0 Variable Turu -Carrier FET Drain 5000 Tune Nom-> Max-> -0.5 -5000 Carrier FET Gate Close Save p26 Restore Tag Sweep Freeze Clear Help Mn-> Step-> Peaking FET Drain -1 -10000 -1539 -1039 -539 -102.7 -2039 Peaking FET Gate Frequency (MHz) -1.5 -5000

-10000

-1452

-952.1

Frequency (MHz)

-452.1

-103.8

Stability Analysis Wizard: Select Circuit Schematic

Stability Analysis

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Next Cancel

1.1

2.1

3.1

Frequency (GHz)

4.1

5.1

6

0.1

Front-to-Back RF GaN PA design

- Determine the biasing requirement
- Linear stability analysis and stabilization network (if needed)
- Impedance matching (source/load pull) and nonlinear optimization
- Physical design and EM extraction
- Optimization
- Yield Analysis
- Digital Modulation Analysis EVM, ACPR, CCDF, Spectrum, IQ results





RF Packaging and Electrothermal Analysis



Why Celsius Thermal Solver in RF Design?

- Operating temperatures impact reliability (device lifetime) and performance
- Thermal analysis gives designers an understanding of operating temperature related to power dissipation
- Temperature information can be inserted into the electrothermal model to predict the impact on RF performance
- Heat maps can be used to help develop/optimize heatsink design
- Provide RF engineers with ready access to operating temperature data for reliability and performance studies



Celsius[™] Thermal Solver



Celsius Thermal Solver for Thermal Analysis in Microwave Office Software

Key features and benefits

- Thermal structures are easily created using powerful Microwave Office[®] extraction block workflow
- Leverages existing structure data (geometries, materials, stack up) in Microwave Office software to define Celsius[™] Thermal Solver structure
- Obtain power dissipation information from Microwave Office analysis
- Thermal simulations launched from inside AWR[®] platform, results automatically returned
- Easy-to-use flow allows RF design engineers to perform their own thermal analysis



Microwave Office / Celsius Thermal Workflow

- 1. Set-up thermal draw layers, EM layer mapping
- 2. Define heat source geometries in layout (or pCell)
- 3. Add extraction block to create a thermal document
- 4. Create **power dissipation** data file from nonlinear simulation (new measurement)
- 5. Associate extraction block with stackup and power dissipation data file
- Simulate in Microwave Office[®] software or send to Celsius[™] Thermal Solver (native editor)
- 7. Operating temps back-annotated into Microwave Office and linked to userdefined heat sources



Thermal Analysis Results – GaN FET Example

- Test structure GaN HEMT devices, combiner network, and source to ground vias
- Celsius[™] results automatically reported listed of all defined heat sources throughout the hierarchal design layout
- Selected thermal analysis results for individual heat sources are highlighted in the layout
- Average and peak temperature across heat source area and power dissipation are reported







Rohde Schwarz – Cadence Collaboration

WinIQSim2 – VSS – VSE Product integration



Visual System Simulator (VSS)

- Part of the Cadence[®] AWR Design Environment[®] platform
- Design and analyze anything from simple RF links to complete comm systems
 - RF budget analysis, RF spur heritage
 - Modeling and time-domain simulation of complete communication links
 - Phased array design, standard communication libraries, etc.

VSS includes models for every component in such systems!



RF System Design and Analysis Flow in VSS



Include in communication system/test bench

The same RF link is used by RF budget, spur analysis, and time domain simulators!

Joint solution: Rohde & Schwarz and Cadence



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Pre-Distorting an RF Amplifier Purely in Simulation

Script controlling both

software packages:

Cadence VSS and R&S VSE

RF simulation of PA in Cadence VSS

DPD Demo	
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PS SNK	
ID=43	
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D=A2	
FILENAME="\waveforms\sim in.wv"	
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CTRFRQ=1.85 GHz SIGDLY=Ignore SIGDLY=Ignore	
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Iterative Direct DPD in R&S VSE

Summary

- With superior electrical performance, GaN HEMT power amplifiers are being widely adopted for commercial and aerospace/defense applications
- To capitalize on this performance, designers need accurate device models, robust nonlinear RF circuit simulation, and specific design tools
- For MMIC-based PAs, designers need to use PDKs authorized by the GaN foundry to ensure simulation accuracy and proper layout
- The successful design and simulation of GaN PAs is based on multiple simulation technologies including EM analysis for parasitic extraction and possibly circuit envelope for simulation-modulated performance metrics
- Packaging plays a key role in thermal dissipation, internal impedance matching, and multi-technology integration

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